

-30V(D-S) P-Channel Enhancement Mode Power MOS FET

General Features

- $V_{DS} = -30V, I_D = -5.1A$
- $R_{DS(ON)} < 105m\Omega @ V_{GS}=-4.5V$
- $R_{DS(ON)} < 55m\Omega @ V_{GS}=-10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

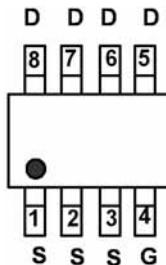


Lead Free

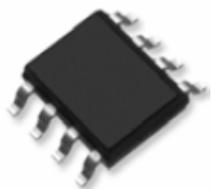
Application

- PWM applications
- Load switch
- Power management

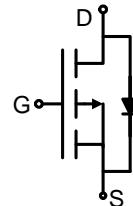
PIN Configuration



Marking and pin Assignment



SOP-8 top view



Schematic diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MSP9435W	MSP9435W	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-5.1	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	-20	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	50	°C/W
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-24\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1	-1.6	-3	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-5.1\text{A}$	-	48	55	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4.2\text{A}$	-	73	105	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-4.5\text{A}$	4	7	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	1040	-	PF
Output Capacitance	C_{oss}		-	420	-	PF
Reverse Transfer Capacitance	C_{rss}		-	150	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=-15\text{V}, I_{\text{D}}=-1\text{A}, V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=6\Omega$	-	15	-	nS
Turn-on Rise Time	t_{r}		-	13	-	nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	58	-	nS
Turn-Off Fall Time	t_{f}		-	21	-	nS
Total Gate Charge	Q_{g}	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-5.1\text{A}, V_{\text{GS}}=-10\text{V}$	-	12	-	nC
Gate-Source Charge	Q_{gs}		-	2.2	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{s}}=-1.7\text{A}$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

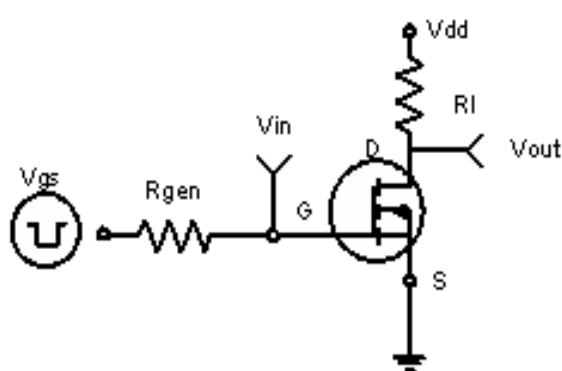


Figure 1:Switching Test Circuit

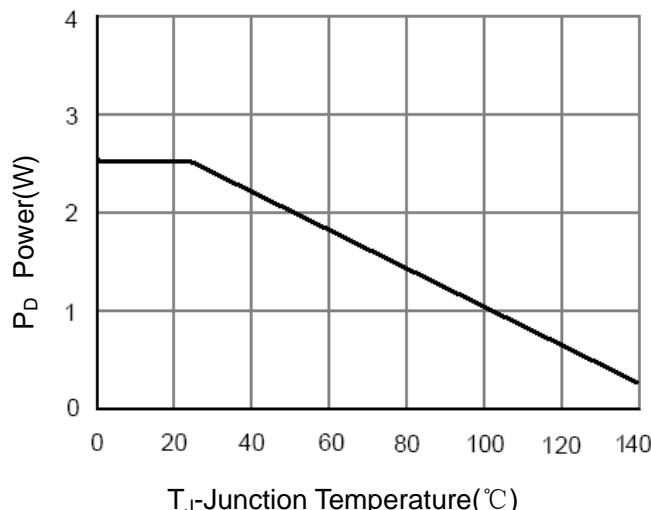


Figure 3 Power Dissipation

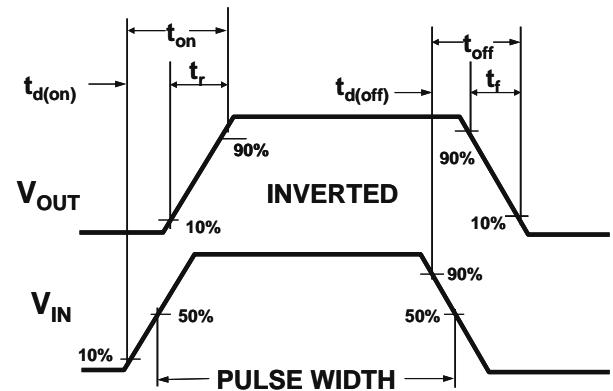


Figure 2:Switching Waveforms

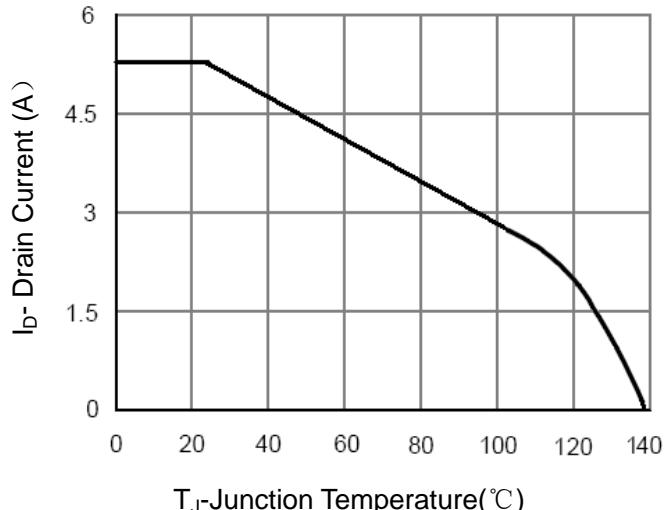


Figure 4 Drain Current

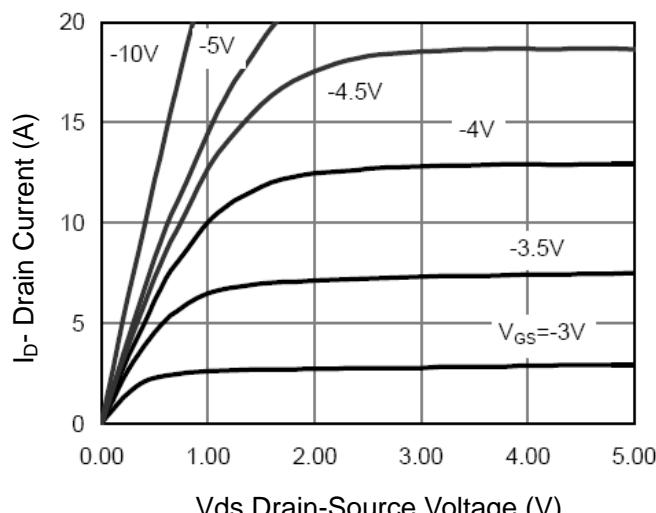


Figure 5 Output Characteristics

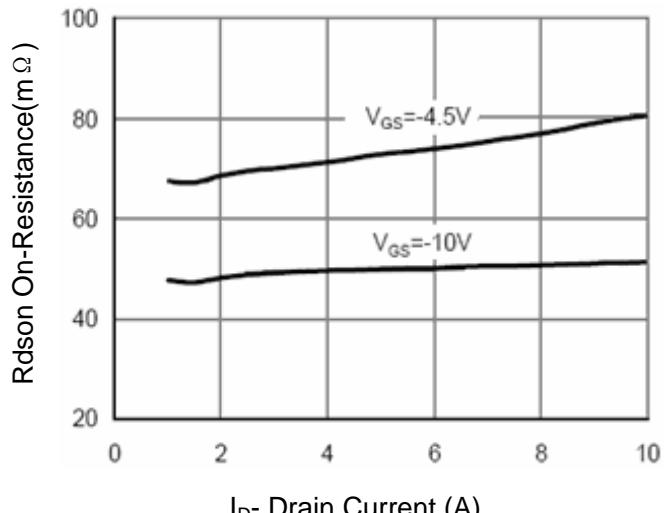
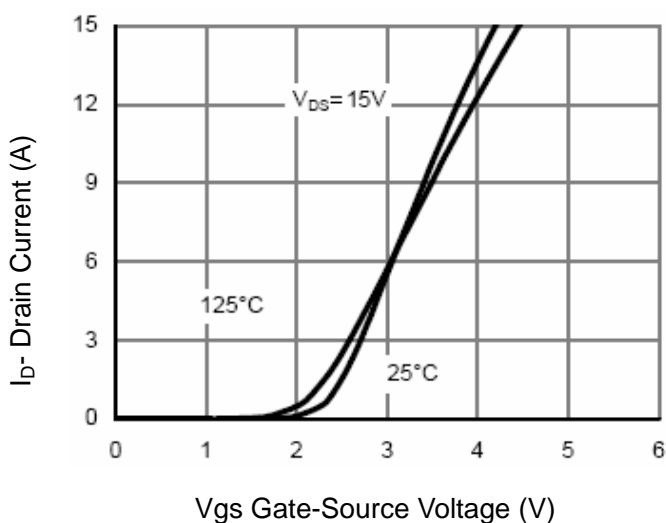
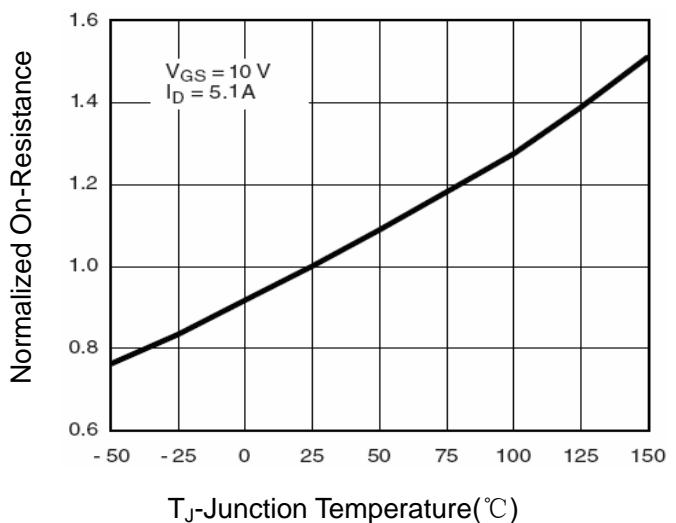
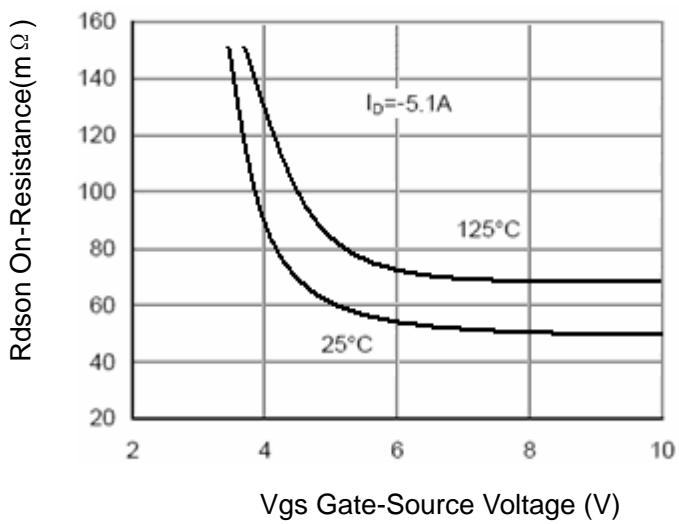
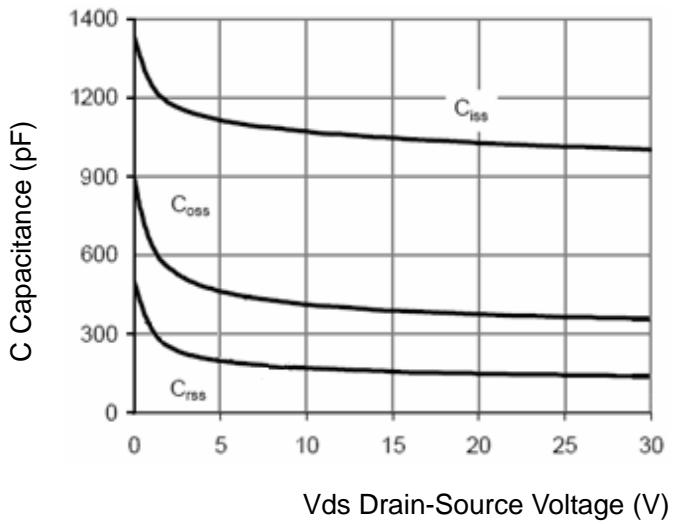
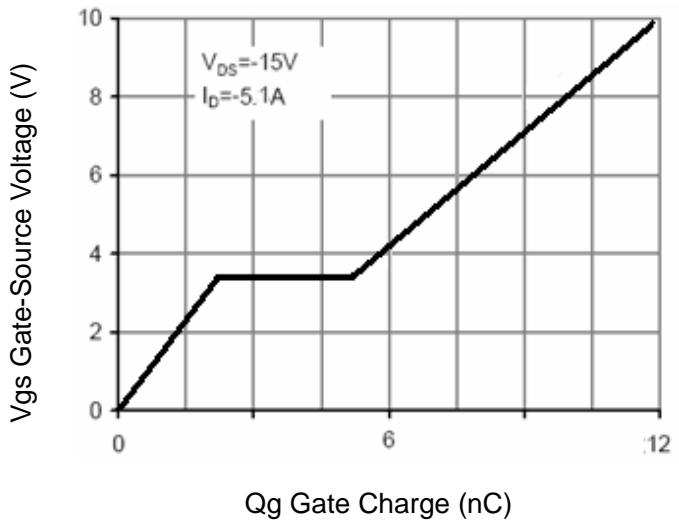
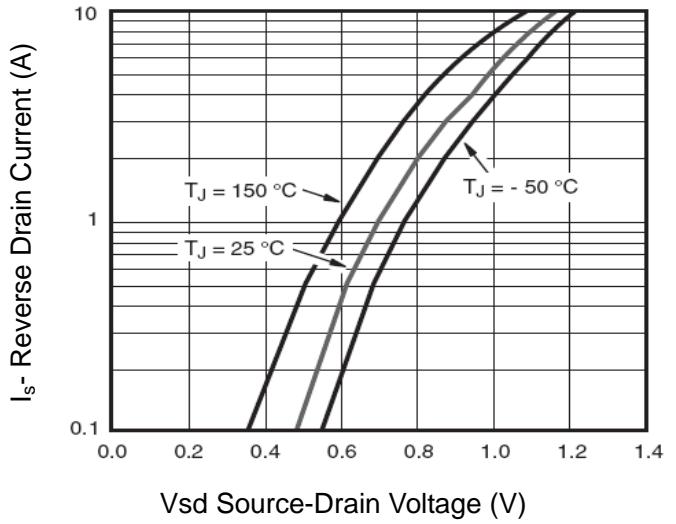
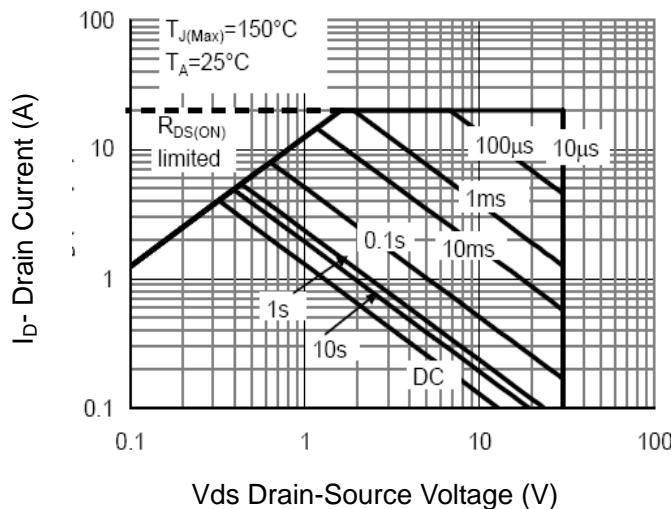
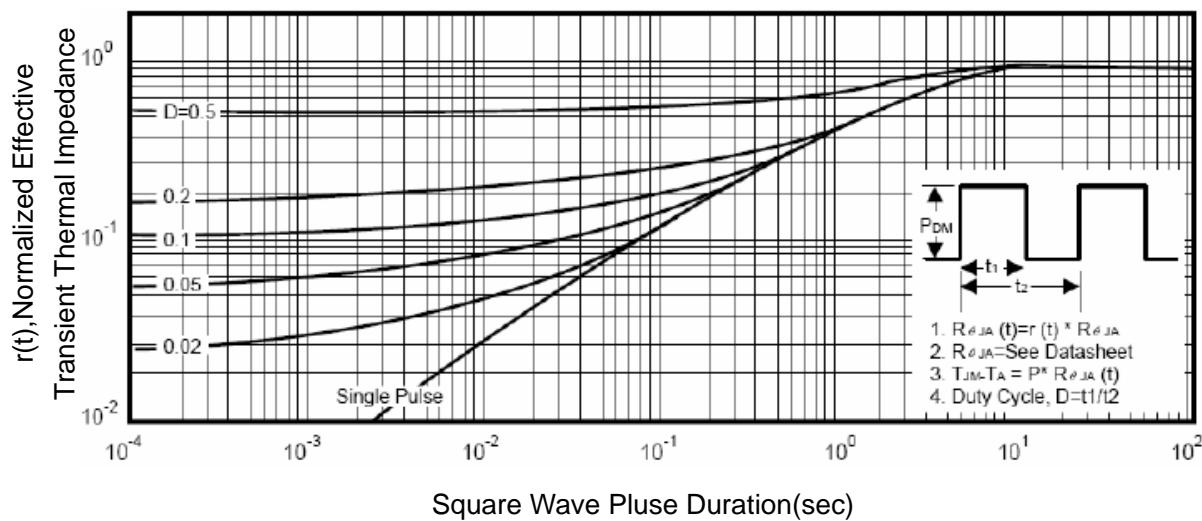
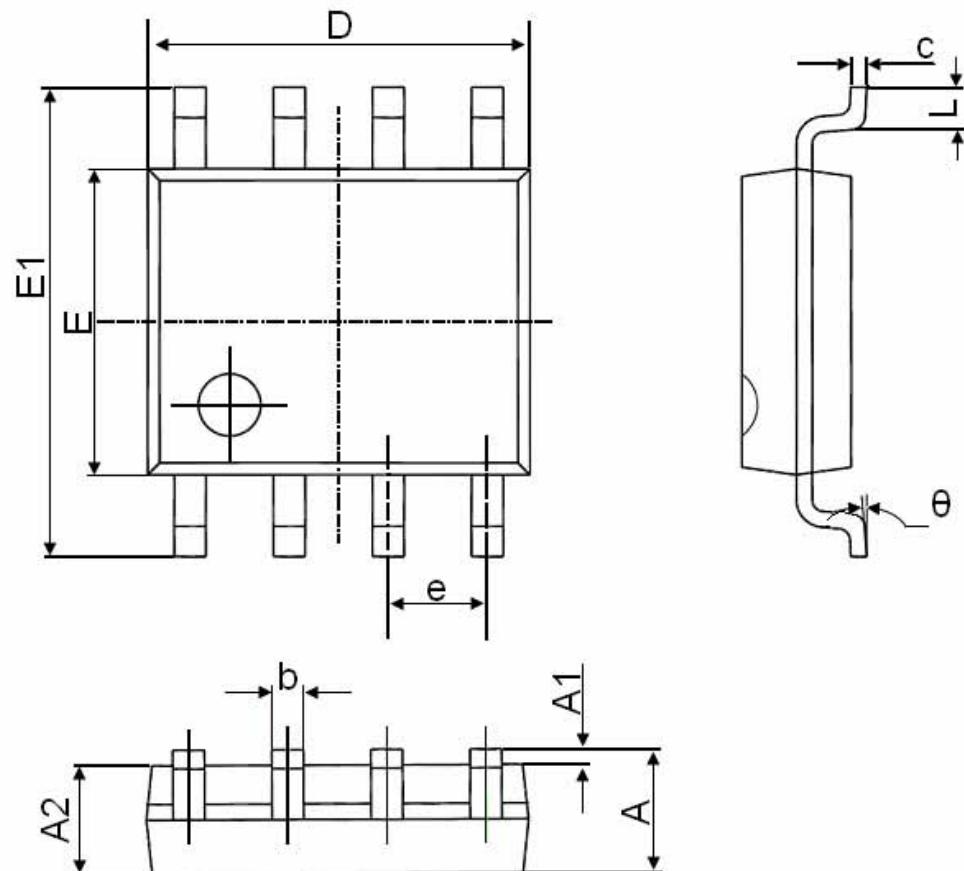


Figure 6 Drain-Source On-Resistance

**Figure 7 Transfer Characteristics****Figure 8 Drain-Source On-Resistance****Figure 9 $R_{DS(on)}$ vs V_{GS}** **Figure 10 Capacitance vs V_{DS}** **Figure 11 Gate Charge****Figure 12 Source-Drain Diode Forward**

**Figure 13 Safe Operation Area****Figure 14 Normalized Maximum Transient Thermal Impedance**

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°